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Team Nexperia



PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, R2 = openRev. 1 — 12 June 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC123TMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	1.54	2.2	2.86	kΩ



PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		3
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 2 sym009

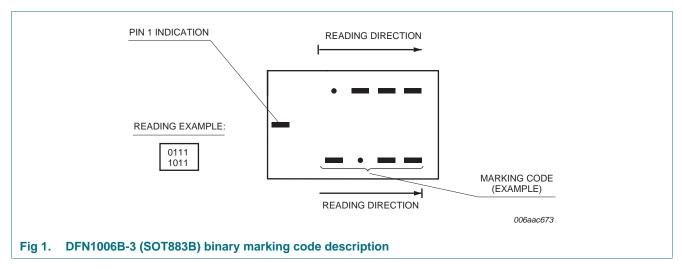
3. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PDTA123TMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B					

4. Marking

Table 4.Marking codes

Type number	Marking code
PDTA123TMB	0010 0011



PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

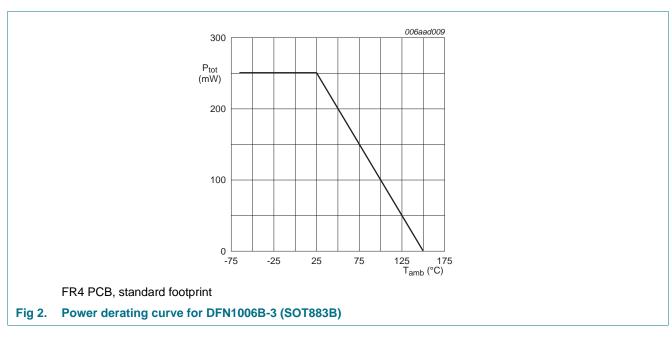
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
l _O	output current			-	-100	mA
I _{CM}	peak collector current	pulsed; t _p ≤ 1 ms		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

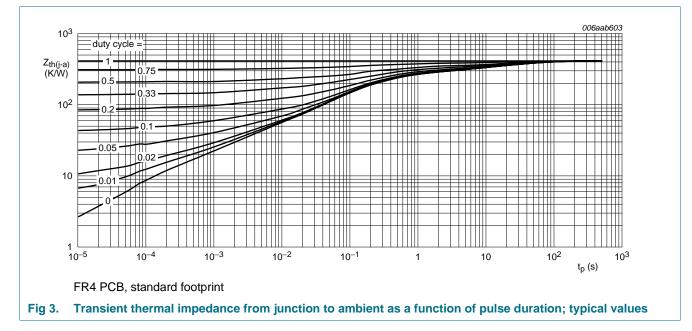
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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PDTA123TMB

PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, R2 = open



7. Characteristics

Table 7. Characteristics

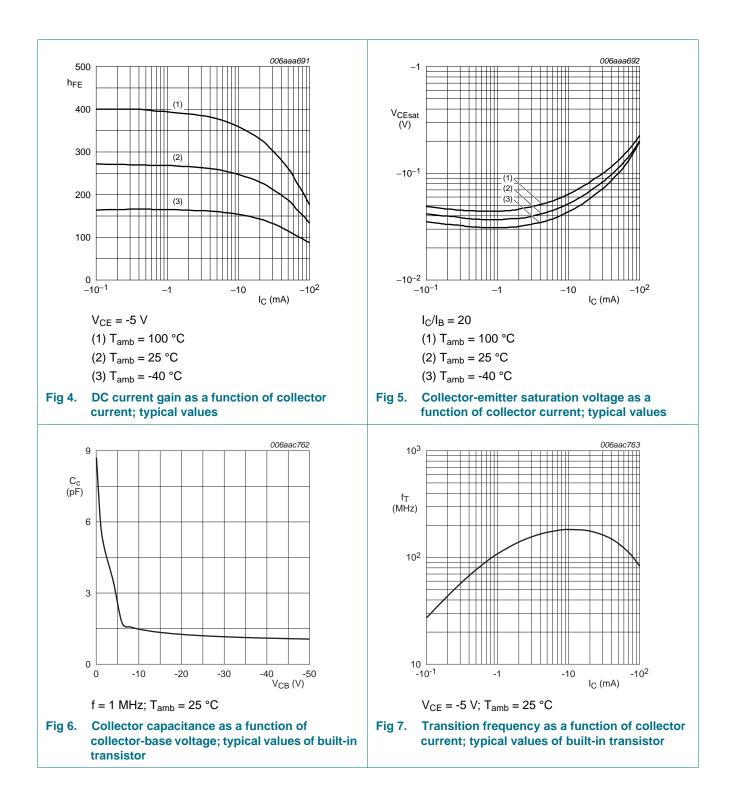
Denematen	O an allthan a		B.4.1.	T	N/	1.1
Parameter	Conditions		Min	тур	мах	Unit
collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	-100	nA
collector-emitter cut-off	V_{CE} = -30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	-1	μA
current	V_{CE} = -30 V; I _B = 0 A; T _j = 150 °C		-	-	-5	μA
emitter-base cut-off current	V_{EB} = -5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	-100	nA
DC current gain	V_{CE} = -5 V; I _C = -20 mA; T _{amb} = 25 °C		30	-	-	
collector-emitter saturation voltage	I_{C} = -10 mA; I_{B} = -0.5 mA; T_{amb} = 25 °C		-	-	-150	mV
bias resistor 1 (input)	T _{amb} = 25 °C		1.54	2.2	2.86	kΩ
collector capacitance	$\label{eq:CB} \begin{array}{l} V_{CB} = -10 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz}; \text{ T}_{amb} = 25 \ ^{\circ}\text{C} \end{array}$		-	-	3	pF
transition frequency	V_{CE} = -5 V; I _C = -10 mA; f = 100 MHz; T _{amb} = 25 °C	<u>[1]</u>	-	180	-	MHz
	current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage bias resistor 1 (input) collector capacitance	$\begin{array}{ll} \mbox{collector-base cut-off} & V_{CB} = -50 \ V; \ I_E = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{current} & V_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{V}_{CE} = -30 \ V; \ I_B = 0 \ A; \ T_{j} = 150 \ ^{\circ}C \\ \mbox{emitter-base cut-off} & V_{EB} = -5 \ V; \ I_C = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{current} & V_{CE} = -5 \ V; \ I_C = -20 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-emitter} & I_C = -10 \ mA; \ I_B = -0.5 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{collector-capacitance} & V_{CB} = -10 \ V; \ I_E = 0 \ A; \ i_e = 0 \ A; \\ \mbox{f} = 1 \ MHz; \ T_{amb} = 25 \ ^{\circ}C \\ \mbox{transition frequency} & V_{CE} = -5 \ V; \ I_C = -10 \ mA; \ f = 100 \ mHz; \end{array}$	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ emitter-base cut-off current $V_{EB} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ collector capacitance $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ i}_e = 0 \text{ A};$ $f = 1 \text{ MHz}; \text{ T}_{amb} = 25 \text{ °C}$ transition frequency $V_{CE} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; f = 100 \text{ MHz};$	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ -collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ -emitter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ -emitter-base cut-off current $V_{EB} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ -DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 30collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ -bias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ 1.54collector capacitance $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ i}_e = 0 \text{ A}; _f = 1 \text{ MHz}; \text{ T}_{amb} = 25 \text{ °C}$ -transition frequency $V_{CE} = -5 \text{ V}; \text{ I}_C = -10 \text{ mA}; \text{ f} = 100 \text{ MHz};$ 11	collector-base cut-off current $V_{CB} = -50 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ witter-base cut-off current $V_{CE} = -30 \text{ V}; \text{ I}_B = 0 \text{ A}; \text{ T}_j = 150 \text{ °C}$ emitter-base cut-off current $V_{EB} = -5 \text{ V}; \text{ I}_C = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$ DC current gain $V_{CE} = -5 \text{ V}; \text{ I}_C = -20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 30-collector-emitter saturation voltage $I_C = -10 \text{ mA}; \text{ I}_B = -0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ 1.542.2collector capacitance $V_{CB} = -10 \text{ V}; \text{ I}_E = 0 \text{ A}; \text{ i}_e = 0 A$	collector-base cut-off current $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ - - - -100 collector-emitter cut-off current $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ - - - -1 vertice $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ - - - -1 vertice $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$ - - -5 emitter-base cut-off current $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ - - -100 DC current gain $V_{CE} = -5 \text{ V}; I_C = -20 \text{ mA}; T_{amb} = 25 \text{ °C}$ - - -100 DC current gain $V_{CE} = -5 \text{ V}; I_C = -20 \text{ mA}; T_{amb} = 25 \text{ °C}$ 30 - - collector-emitter saturation voltage $I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ - - -150 bias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ 1.54 2.2 2.86 collector capacitance $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$ - - 3 transition frequency $V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA}; f = 100 \text{ MHz};$ 11 - 180 </td

[1] Characteristics of built-in transistor.

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PDTA123TMB

PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open



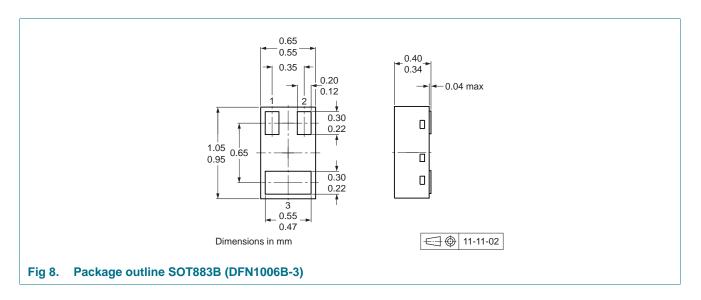
PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, R2 = open

8. Test information

8.1 Quality information

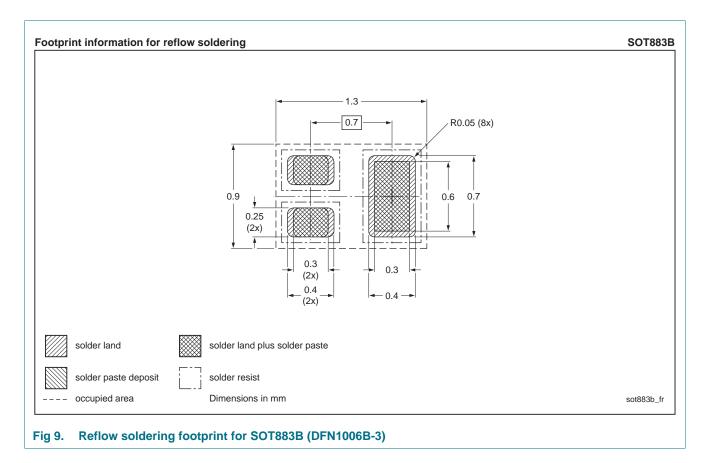
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

10. Soldering



PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

11. Revision history

Table 8. Revision	8. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PDTA123TMB v.1	20120612	Product data sheet	-	-				

PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product data sheet

PDTA123TMB

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PNP resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, R2 = open

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PNP resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

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Date of release: 12 June 2012 Document identifier: PDTA123TMB

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